

TOSHIBA PHOTOCOUPLER GaAs IRED &amp; PHOTO-TRIAC

## T L P 3 0 6 4

OFFICE MACHINE

HOUSEHOLD USE EQUIPMENT

TRIAC DRIVER

SOLID STATE RELAY

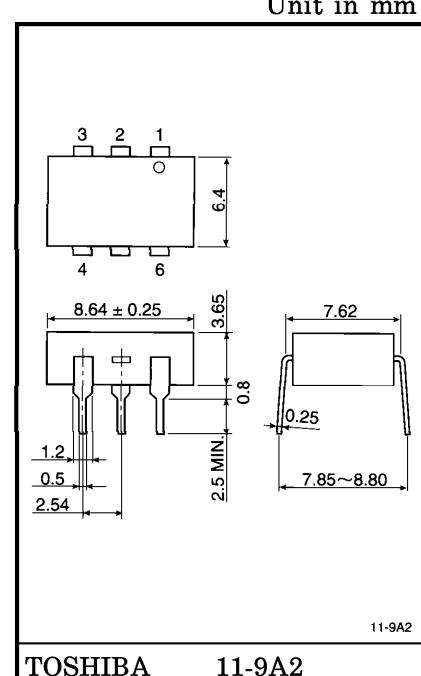
The TOSHIBA TLP3064 consists of a zero voltage crossing turn-on photo-triac optically coupled to a GaAlAs infrared emitting diode in a six lead plastic DIP package.

- Peak Off-State Voltage : 600V (Min.)
- Trigger LED Current : 3mA (Max.)
- On-State Current : 100mA (Max.)
- Isolation Voltage : 5000Vrms (Min.)
- UL Recognized : UL1577, File No. E67349
- Option (D4) type  
VDE Approved : DIN VDE0884 / 06.92,  
Certificate No. 83649

Maximum Operating Insulation Voltage : 890V<sub>PK</sub>Highest Permissible Over Voltage : 8000V<sub>PK</sub>

(Note) When a VDE0884 approved type is needed,  
please designate the "Option (D4)"

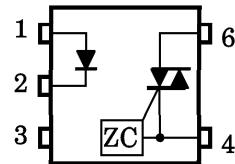
|                      | 7.62mm pitch<br>standard type | 10.16mm pitch<br>(LF2) type |
|----------------------|-------------------------------|-----------------------------|
| • Creepage Distance  | : 7.0mm (Min.)                | 8.0mm (Min.)                |
| Clearance            | : 7.0mm (Min.)                | 8.0mm (Min.)                |
| Insulation Thickness | : 0.5mm (Min.)                | 0.5mm (Min.)                |



TOSHIBA 11-9A2

Weight : 0.44g

## PIN CONFIGURATIONS (TOP VIEW)



- 1: ANODE
- 2: CATHODE
- 3: N.C.
- 4: TERMINAL 1
- 6: TERMINAL 2

(ZC : Zero-cross Circuit)

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

| CHARACTERISTIC  |  | SYMBOL                        | RATING  | UNIT                  |
|---|--|-------------------------------|---------|-----------------------|
| LED   | Forward Current  | $I_F$                         | 30      | mA                    |
|   | Forward Current Derating ( $T_a \geq 25^\circ\text{C}$ )           | $\Delta I_F / ^\circ\text{C}$ | -0.3    | mA / $^\circ\text{C}$ |
|   | Peak Forward Current (100 $\mu\text{s}$ pulse, 100pps)             | $I_{FP}$                      | 1       | A                     |
|   | Reverse Voltage  | $V_R$                         | 5       | V                     |
|   | Junction Temperature   | $T_j$                         | 125     | $^\circ\text{C}$      |
| DETECTOR  | Off-State Output Terminal Voltage                                  | $V_{DRM}$                     | 600     | V                     |
|   | On-State RMS Current   | $I_T(\text{RMS})$             | 100     | mA                    |
|   | $T_a = 70^\circ\text{C}$   |                               | 50      |                       |
|   | On-State Current Derating ( $T_a \geq 25^\circ\text{C}$ )          | $\Delta I_T / ^\circ\text{C}$ | -1.1    | mA / $^\circ\text{C}$ |
|   | Peak On-State Current (100 $\mu\text{s}$ pulse, 120pps)            | $I_{TP}$                      | 2       | A                     |
|   | Peak Nonrepetitive Surge Current ( $P_W = 10\text{ms}$ , DC = 10%) | $I_{TSM}$                     | 1.2     | A                     |
|   | Junction Temperature   | $T_j$                         | 115     | $^\circ\text{C}$      |
|   | Storage Temperature Range  | $T_{stg}$                     | -55~150 | $^\circ\text{C}$      |
|   | Operating Temperature Range  | $T_{opr}$                     | -40~100 | $^\circ\text{C}$      |
| Lead Soldering Temperature (10s)                          |  | $T_{sol}$                     | 260     | $^\circ\text{C}$      |
| Isolation Voltage (AC, 1min., R.H. $\leq 60\%$ ) (Note 1) |  | $B_{VS}$                      | 5000    | Vrms                  |

(Note 1) Device considered a two terminal device=Pins 1, 2 and 3 shorted together and pins 4 and 6 shorted together.

## RECOMMENDED OPERATING CONDITIONS

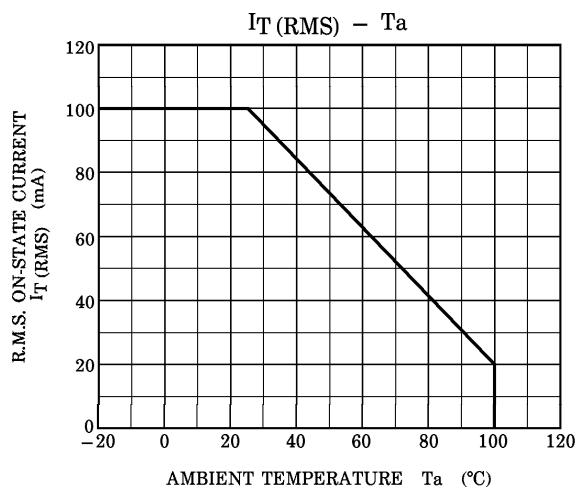
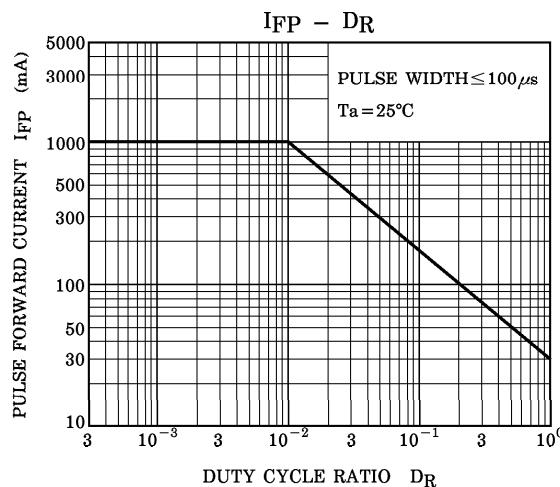
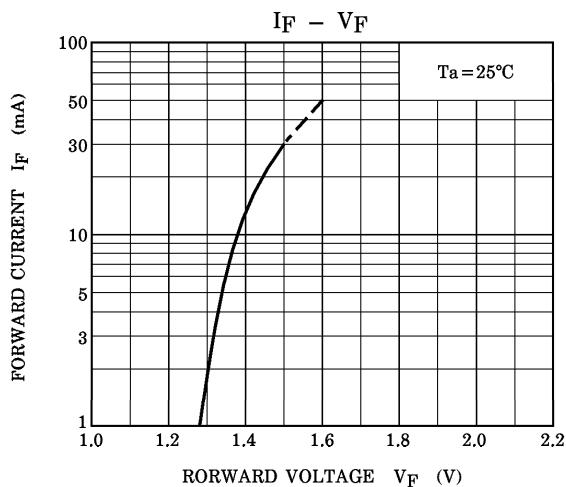
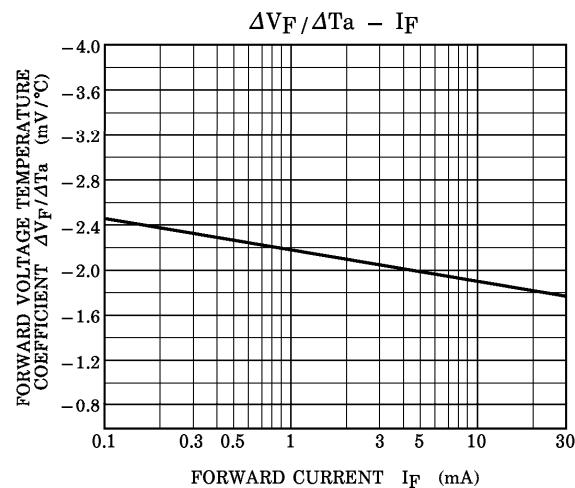
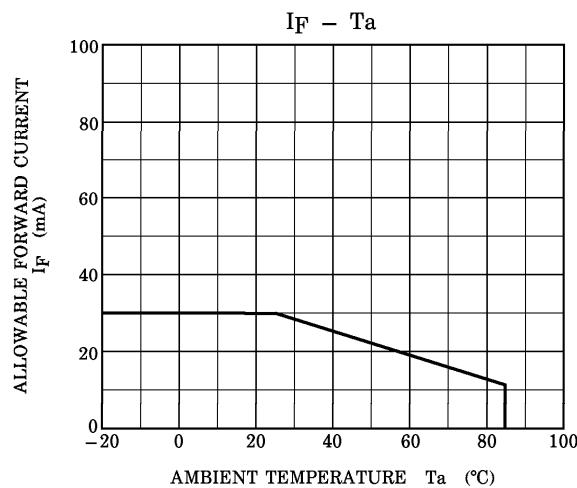
| CHARACTERISTIC        | SYMBOL    | MIN. | TYP. | MAX. | UNIT             |
|-----------------------|-----------|------|------|------|------------------|
| Supply Voltage        | $V_{AC}$  | —    | —    | 240  | Vac              |
| Forward Current       | $I_F$     | 4.5  | 6    | 7.5  | mA               |
| Peak On-State Current | $I_{TP}$  | —    | —    | 1    | A                |
| Operating Temperature | $T_{opr}$ | -10  | —    | 85   | $^\circ\text{C}$ |

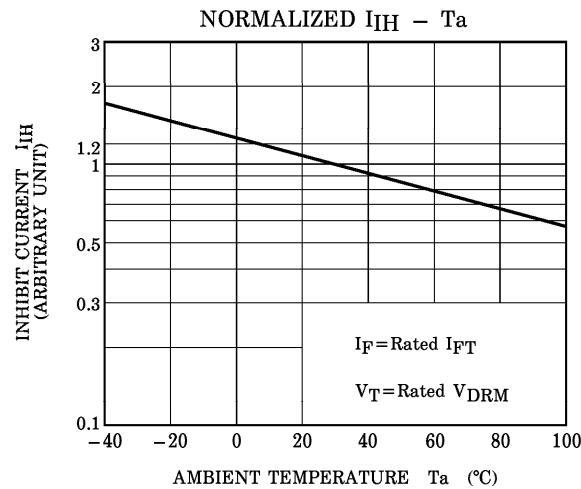
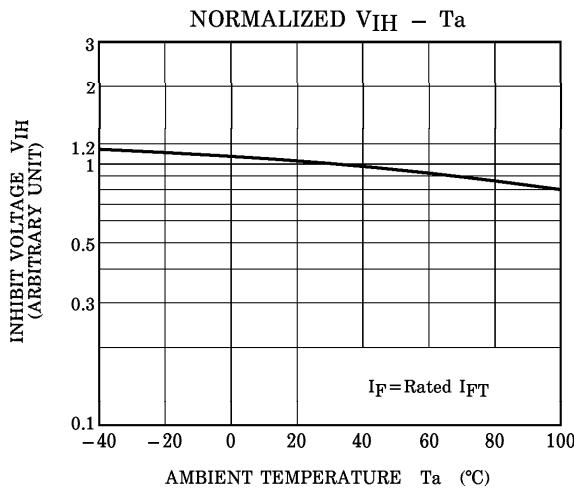
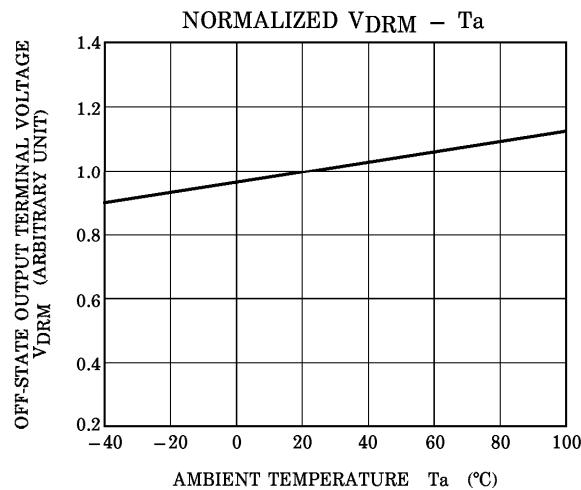
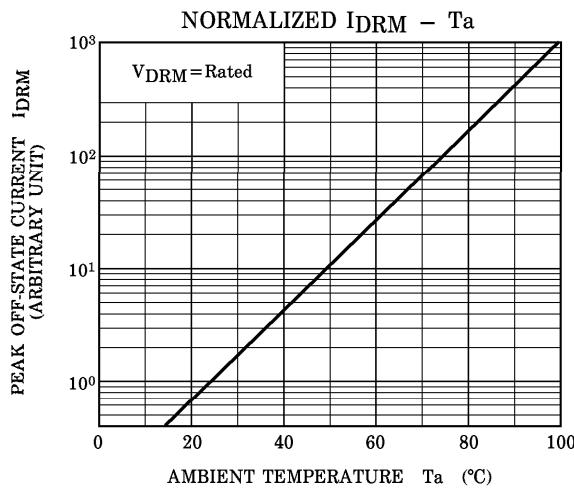
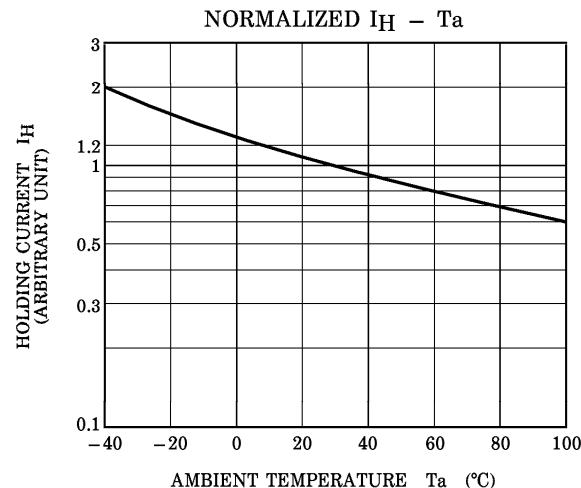
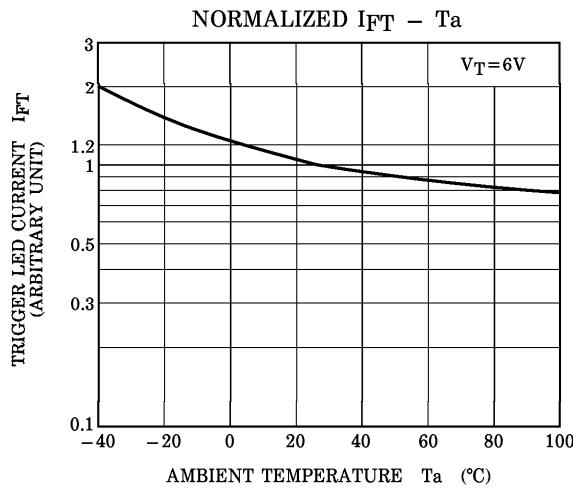
## INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC |  | SYMBOL           | TEST CONDITION                                      | MIN. | TYP. | MAX. | UNIT   |
|----------------|--|------------------|---|------|------|------|--------|
| LED            | Forward Voltage                              | V <sub>F</sub>   | I <sub>F</sub> =10mA                                | 1.2  | 1.4  | 1.7  | V      |
|                | Reverse Current                              | I <sub>R</sub>   | V <sub>R</sub> =3V                                  | —    | —    | 10   | μA     |
|                | Capacitance                                  | C <sub>T</sub>   | V=0, f=1MHz   | —    | 30   | —    | pF     |
| DETECTOR       | Peak Off-State Current                       | I <sub>DRM</sub> | V <sub>DRM</sub> =600V                              | —    | 10   | 1000 | nA     |
|                | Peak On-State Voltage                        | V <sub>TM</sub>  | I <sub>TM</sub> =100mA                              | —    | —    | 3.0  | V      |
|                | Holding Current                              | I <sub>H</sub>   | —   | —    | 0.6  | —    | mA     |
|                | Critical Rate of Rise of Off-State Voltage   | dv / dt          | V <sub>in</sub> =240rms<br>Ta=85°C                  | 200  | 500  | —    | V / μs |
|                | Critical Rate of Rise of Commutating Voltage | dv / dt(c)       | V <sub>in</sub> =60Vrms<br>I <sub>T</sub> =15mA rms | —    | 0.2  | —    | V / μs |

## COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC              | SYMBOL          | TEST CONDITION  | MIN.               | TYP.             | MAX. | UNIT |
|-----------------------------|-----------------|---|--------------------|------------------|------|------|
| Trigger LED Current         | I <sub>FT</sub> | V <sub>T</sub> =6V, Resistive Load  | —                  | —                | 3    | mA   |
| Inhibit Voltage             | V <sub>IH</sub> | I <sub>F</sub> =Rated I <sub>FT</sub>   | —                  | —                | 50   | V    |
| Leakage in Inhibited State  | I <sub>IH</sub> | I <sub>F</sub> =Rated I <sub>FT</sub><br>V <sub>T</sub> =Rated V <sub>DRM</sub> | —                  | —                | 600  | μA   |
| Capacitance Input to Output | C <sub>S</sub>  | V <sub>S</sub> =0, f=1MHz   | —                  | 0.8              | —    | pF   |
| Isolation Resistance        | R <sub>S</sub>  | V <sub>S</sub> =500V, R.H.≤60%  | 1×10 <sup>12</sup> | 10 <sup>14</sup> | —    | Ω    |
| Isolation Voltage           | BVS             | AC, 1 minute  | 5000               | —                | —    | Vrms |
|                             |                 | AC, 1 second, in oil  | —                  | 10000            | —    |      |
|                             |                 | DC, 1 minute, in oil  | —                  | 10000            | —    | Vdc  |





## RESTRICTIONS ON PRODUCT USE

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